

GR-65P150LT: TO-252 Cascode GaN HEMT

Description

GR-65P150LT is a normally-off GaN High electron mobility transistor (HEMT) device using the cascode configuration, which provides high breakdown voltage, high current and high operating speed which is suitable for high power applications.

Key Specifications

Part Number	GR-65P150LT
V _{DSS} , min.	650V
R _{DS(ON)} , typ.	147mΩ
Package	TO-252

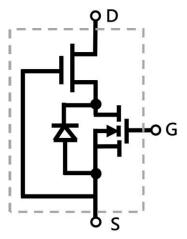
GR-65P150LT (TO-252)

Features

- Gate drive voltage compatibility (-20V to +20V)
- High operating frequency
- Pin to Pin with CoolMOS/SJ and SiC MOSFET
- Low Qrr

Applications

- Switch Mode Power Supplies (SMPS)
- AC-DC/ DC-DC Converters
- Motor Drives



Cascode Device Structure